

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

B. Amendments to the Claims.

Claims 1-4 (Cancelled)

5. (Original) A semiconductor device, comprising:

a metal base having a bottom portion formed from a metal plate and at least two side portions situated upward from the bottom portion, the at least two side portions having notches therein to form upper and lower edges in the side portions, the upper edges being connection electrodes for mounting the semiconductor device to a mounting surface; and

a semiconductor chip mounted to the bottom portion of the metal base having a surface with surface electrodes for mounting the semiconductor device to the mounting surface.

6. (Original) The semiconductor device of claim 5, wherein:

each of the connection electrodes has an area that is less than any of the surface electrodes.

7. (Original) The semiconductor device of claim 5, wherein:

the connection electrodes are symmetrical about a first axis that is parallel to the side portions, and symmetrical about a second axis that is perpendicular to the first axis.

8. (Original) The semiconductor device of claim 5, wherein:

the metal base includes grooves along a border between the bottom portion and each side portion.

Claim 9 (Cancelled)

10. (Original) The semiconductor device of claim 5, wherein:

the surface electrodes of the semiconductor chip are at a first surface level;
and

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

the connection electrodes are at a second surface level higher than the first surface level by a predetermined distance that is greater than 0 mm and less than or equal to 0.1 mm.

11. (Currently Amended) The semiconductor device of claim 5, wherein:

~~the~~ solder balls or bumps are formed on the at least one of the connection electrodes and one of the surface electrodes.

12. (Original) The semiconductor device of claim 5, wherein:

the semiconductor chip is an insulated gate field effect transistor (IGFET) having a drain electrode formed on a rear surface in direct electrical contact with the bottom portion of the metal base so that the at least one connection electrode is a drain connection electrode, and the surface electrodes include a gate electrode and source electrode for the IGFET.

Claims 13-22 (Cancelled)